CPH6355

Power MOSFET -30V, $169m\Omega$, -3A, Single P-Channel



www.onsemi.com

Features

- Low ON-Resistance
- 4V Drive
- Pb-Free, Halogen Free and RoHS Compliance

VDSS	R _{DS} (on) Max	ID Max
	169mΩ@ -10V	
-30V	276mΩ@ -4.5V	-3A
	313mΩ@ –4V	

Specifications

Absolute Maximum Ratings at Ta = 25°C

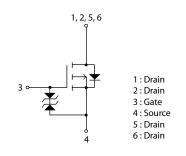
Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	-30	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	-3	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	IDP	-12	А
Power Dissipation When mounted on ceramic substrate (1500mm² × 0.8mm)	PD	1.6	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

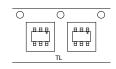
Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (1500mm ² × 0.8mm)	R _{θJA}	78.1	°C/W

Electrical Connection P-Channel



Packing Type: TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

^{*} Machine Model

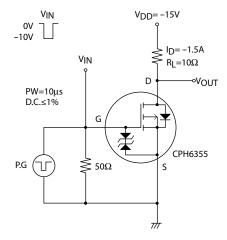
CPH6355

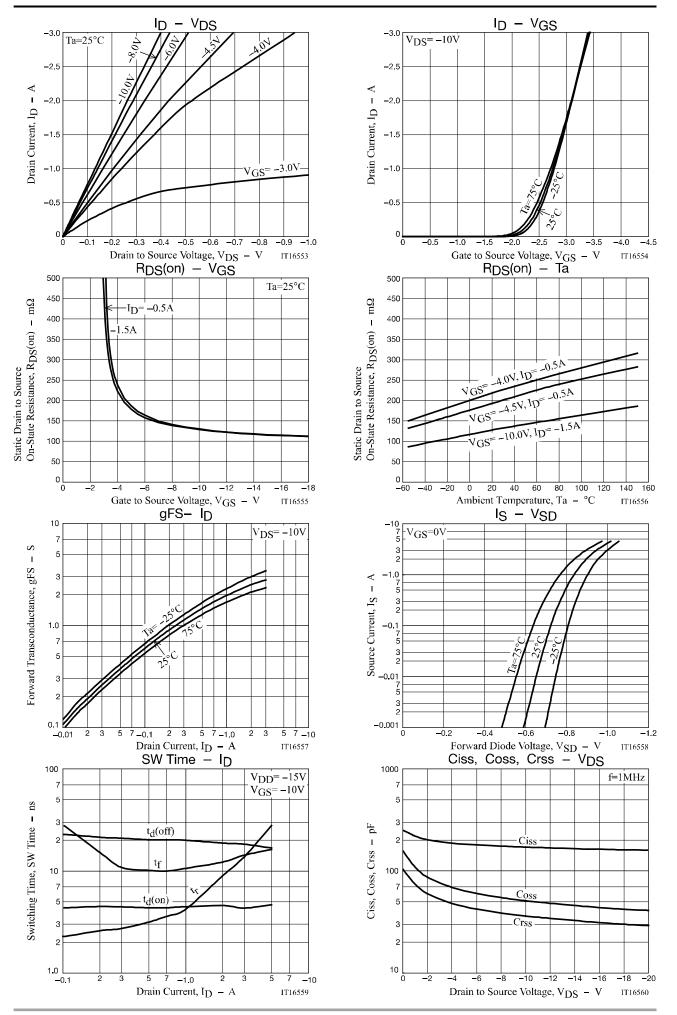
Electrical Characteristics at Ta = 25°C

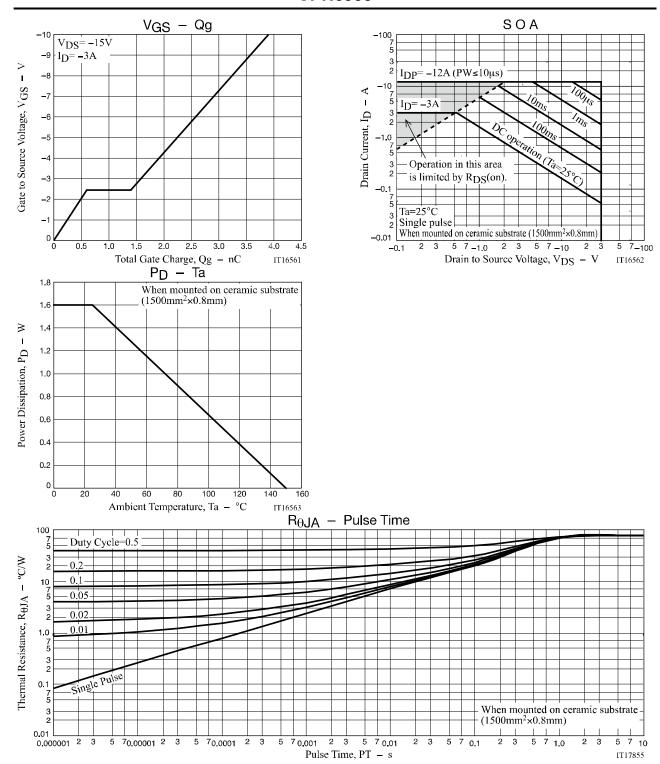
Parameter	Symbol	O contitions	Value			11.2
		Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-30V, V _{GS} =0V			-1	μА
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transconductance	9FS	V _{DS} =-10V, I _D =-1.5A		2.3		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =-1.5A, V _{GS} =-10V		130	169	mΩ
	R _{DS} (on)2	I _D =-0.5A, V _{GS} =-4.5V		197	276	mΩ
	R _{DS} (on)3	I _D =-0.5A, V _{GS} =-4V		223	313	mΩ
Input Capacitance	Ciss			172		pF
Output Capacitance	Coss	V _{DS} =–10V, f=1MHz		51		pF
Reverse Transfer Capacitance	Crss			36		pF
Turn-ON Delay Time	t _d (on)			4.6		ns
Rise Time	t _r			6.6		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		19.4		ns
Fall Time	t _f			11.4		ns
Total Gate Charge	Qg			3.9		nC
Gate to Source Charge	Qgs	V _{DS} =-15V, V _{GS} =-10V, I _D =-3A		0.6		nC
Gate to Drain "Miller" Charge	Qgd	7		8.0		nC
Forward Diode Voltage	V _{SD}	I _S =-3A, V _{GS} =0V		-0.95	-1.5	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit







Package Dimensions

CPH6355-TL-H / CPH6355-TL-W

CPH₆

CASE 318BD ISSUE O

Unit: mm

1: Drain

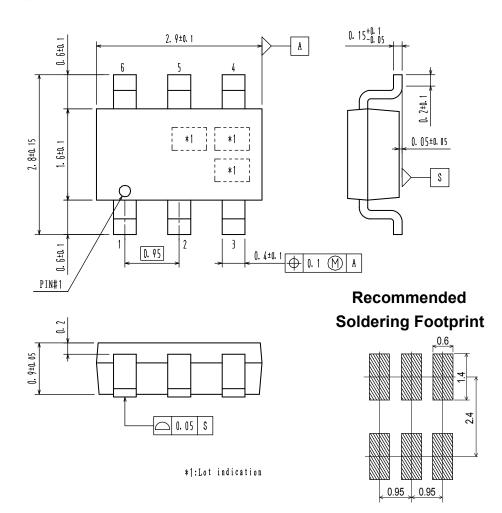
2: Drain

3: Gate

4 : Source

5: Drain

6: Drain



ORDERING INFORMATION

Device	Package	Shipping	Note
CPH6355-TL-H	CPH6, SC-74	3,000 pcs. / Tape & Reel	Pb-Free and
CPH6355-TL-W	355-TL-W SOT-26, SOT-457	5,000 pcs. / Tape & Reel	Halogen Free

Note on usage: Since the CPH6355 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent re

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B